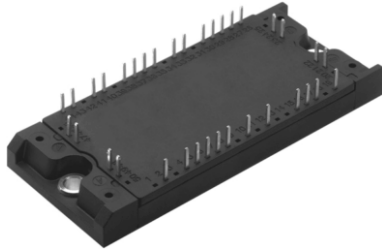


IGBT Fourpack Module, 75 A


ECONO2 4PACK

FEATURES

- Square RBSOA
- HEXFRED® low Q_{rr} , low switching energy
- Positive $V_{CE(on)}$ temperature coefficient
- Copper baseplate
- Low stray inductance design
- Speed 8 kHz to 60 kHz
- Compliant to RoHS directive 2002/95/EC


RoHS
COMPLIANT

PRODUCT SUMMARY

V_{CES}	1200 V
I_C at $T_C = 67\text{ °C}$	75 A
$V_{CE(on)}$ (typical)	3.4 V

BENEFITS

- Benchmark efficiency for SMPS application in particular HF welding
- Rugged transient performance
- Low EMI, requires less snubbing
- Direct mounting to heatsink space saving
- PCB solderable terminals
- Low junction to case thermal resistance

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		1200	V
Continuous collector current	I_C	$T_C = 25\text{ °C}$	100	A
		$T_C = 80\text{ °C}$	67	
Pulsed collector current See fig. C.T.5	I_{CM}		200	
Clamped inductive load current	I_{LM}		200	
Diode continuous forward current	I_F	$T_C = 25\text{ °C}$	60	
		$T_C = 80\text{ °C}$	40	
Diode maximum forward current	I_{FM}		150	
Gate to emitter voltage	V_{GE}		± 20	V
Maximum power dissipation (IGBT)	P_D	$T_C = 25\text{ °C}$	480	W
		$T_C = 80\text{ °C}$	270	
Maximum operating junction temperature	T_J		150	°C
Storage temperature range	T_{Stg}		- 40 to + 125	
Isolation voltage	V_{ISOL}		AC 2500 (MIN)	V



ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{BR(CE)}$	$V_{GE} = 0\text{ V}, I_C = 500\text{ }\mu\text{A}$	1200	-	-	V
Collector to emitter voltage	$V_{CE(ON)}$	$I_C = 75\text{ A}, V_{GE} = 15\text{ V}$	-	3.4	4.0	
		$I_C = 100\text{ A}, V_{GE} = 15\text{ V}$	-	3.8	4.5	
		$I_C = 75\text{ A}, V_{GE} = 15\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	4.0	4.5	
		$I_C = 100\text{ A}, V_{GE} = 15\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	4.53	5.1	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 250\text{ }\mu\text{A}$	4.0	5.0	6.0	
Threshold voltage temperature coefficient	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$ (25 °C to 125 °C)	-	- 11	-	mV/°C
Zero gate voltage collector current	I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$	-	7	250	μA
		$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	580	2000	
Diode forward voltage drop	V_{FM}	$I_F = 75\text{ A}$	-	3.7	4.9	V
		$I_F = 100\text{ A}$	-	4.1	5.5	
		$I_F = 75\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	3.7	5.1	
		$I_F = 100\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	4.2	5.7	
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	± 200	nA

SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Total gate charge (turn-on)	Q_G	$I_C = 75\text{ A}$ $V_{CC} = 600\text{ V}$ $V_{GE} = 15\text{ V}$	-	630	-	nC	
Gate to emitter charge (turn-on)	Q_{GE}		-	65	-		
Gate to collector charge (turn-on)	Q_{GC}		-	250	-		
Turn-on switching loss	E_{on}	$I_C = 75\text{ A}, V_{CC} = 600\text{ V}$ $V_{GE} = 15\text{ V}, R_g = 5\text{ }\Omega, L = 500\text{ }\mu\text{H}$ $T_J = 25\text{ }^\circ\text{C}$ (1)	-	1.74	-	mJ	
Turn-off switching loss	E_{off}		-	1.46	-		
Total switching loss	E_{tot}		-	3.20	-		
Turn-on switching loss	E_{on}		-	2.44	-		
Turn-off switching loss	E_{off}	$I_C = 75\text{ A}, V_{CC} = 600\text{ V}$ $V_{GE} = 15\text{ V}, R_g = 5\text{ }\Omega, L = 500\text{ }\mu\text{H}$ $T_J = 125\text{ }^\circ\text{C}$ (1)	-	2.35	-	mJ	
Total switching loss	E_{tot}		-	4.79	-		
Turn-on delay time	$t_{d(on)}$		-	268	-		
Rise time	t_r	$I_C = 75\text{ A}, V_{CC} = 600\text{ V}$ $V_{GE} = 15\text{ V}, R_g = 5\text{ }\Omega, L = 500\text{ }\mu\text{H}$ $T_J = 125\text{ }^\circ\text{C}$	-	43	-	ns	
Turn-off delay time	$t_{d(off)}$		-	308	-		
Fall time	t_f		-	127	-		
Reverse bias safe operating area	RBSOA	$T_J = 150\text{ }^\circ\text{C}, I_C = 200\text{ A}$ $R_g = 10\text{ }\Omega, V_{GE} = 15\text{ V to } 0\text{ V}$	Fullsquare				
Short circuit safe operating area	SCSOA	$T_J = 150\text{ }^\circ\text{C}$ $V_{CC} = 900\text{ V}, V_P = 1200\text{ V}$ $R_g = 10\text{ }\Omega, V_{GE} = 15\text{ V to } 0\text{ V}$	10	-	-	μs	
Diode peak reverse recovery current	I_{rr}	$V_{CC} = 200\text{ V}$ $I_F = 50\text{ A}$ $di/dt = 10\text{ A}/\mu\text{s}$	$T_J = 25\text{ }^\circ\text{C}$	-	13	18	A
			$T_J = 125\text{ }^\circ\text{C}$	-	19	23	
Diode reverse recovery time	t_{rr}		$T_J = 25\text{ }^\circ\text{C}$	-	132	189	ns
			$T_J = 125\text{ }^\circ\text{C}$	-	200	270	
Total reverse recovery charge	Q_{rr}		$T_J = 25\text{ }^\circ\text{C}$	-	858	1700	nC
			$T_J = 125\text{ }^\circ\text{C}$	-	1900	3105	

Note

(1) Energy losses include “tail” and diode reverse recovery

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
Junction to case IGBT	R_{thJC} (IGBT)	-	-	0.26	°C/W
Junction to case DIODE	R_{thJC} (DIODE)	-	-	0.56	
Case to sink, flat, greased surface	R_{thCS} (MODULE)	-	0.02	-	
Mounting torque (M5)		2.7	-	3.3	Nm
Weight		-	170	-	g

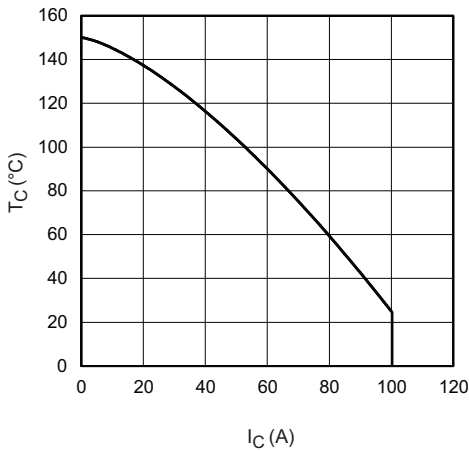


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

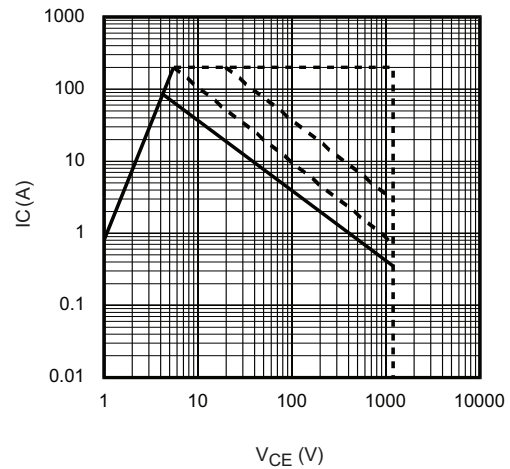
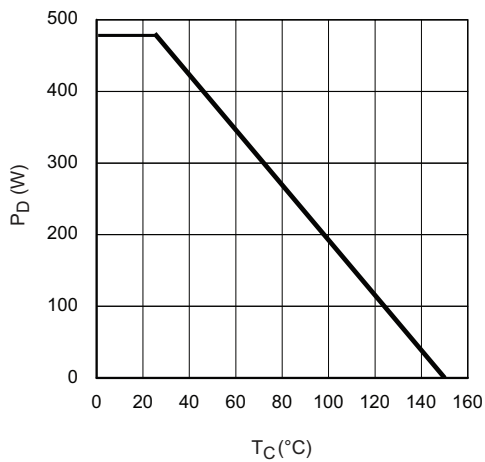
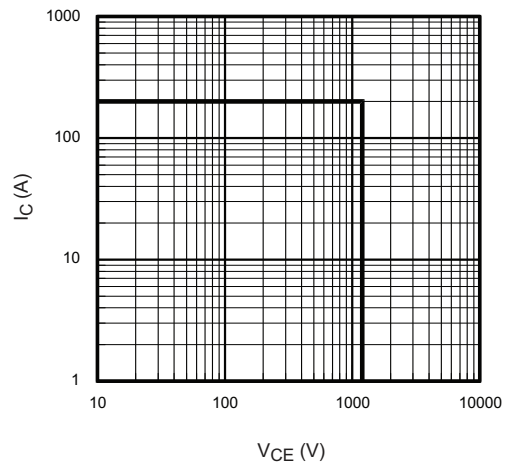

 Fig. 3 - Forward SOA
 $T_C = 25\text{ }^\circ\text{C}$; $T_J \leq 150\text{ }^\circ\text{C}$


Fig. 2 - Power Dissipation vs. Case Temperature


 Fig. 4 - Reverse Bias SOA
 $T_J = 150\text{ }^\circ\text{C}$; $V_{GE} = 15\text{ V}$

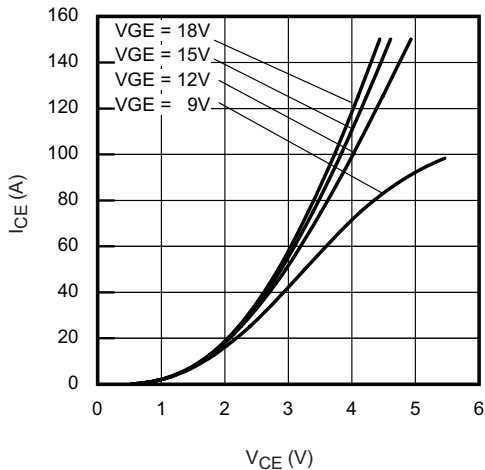


Fig. 5 - Typical IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p = 500 \mu\text{s}$

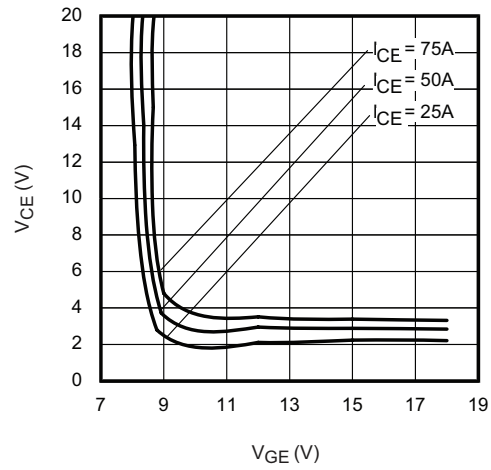


Fig. 8 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

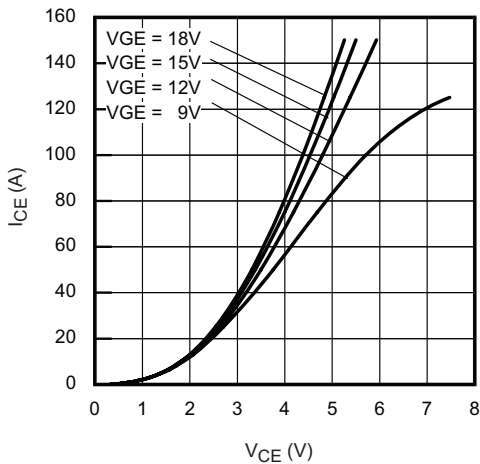


Fig. 6 - Typical IGBT Output Characteristics
 $T_J = 125^\circ\text{C}$; $t_p = 500 \mu\text{s}$

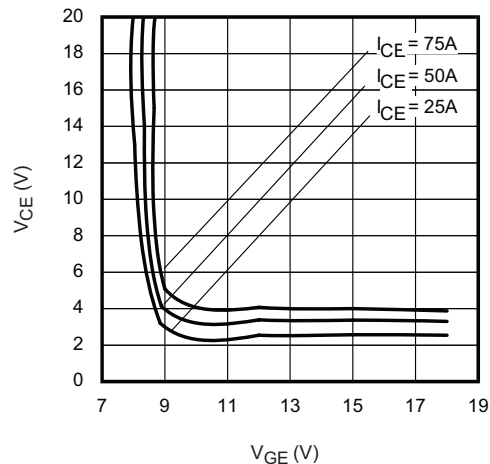


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = 125^\circ\text{C}$

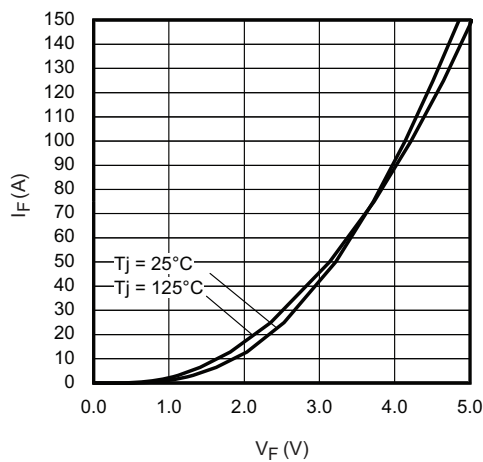


Fig. 7 - Typical Diode Forward Characteristics
 $t_p = 500 \mu\text{s}$

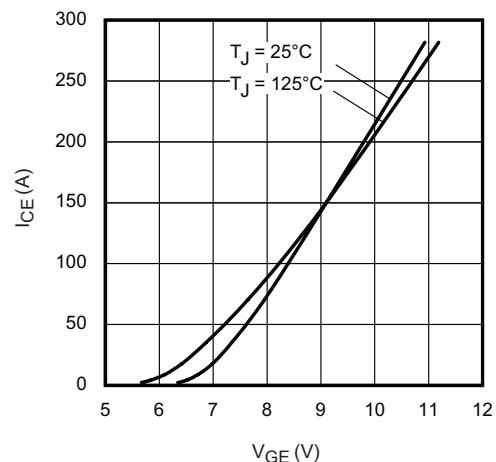


Fig. 10 - Typical Transfer Characteristics
 $V_{CE} = 20 \text{ V}$; $t_p = 500 \mu\text{s}$

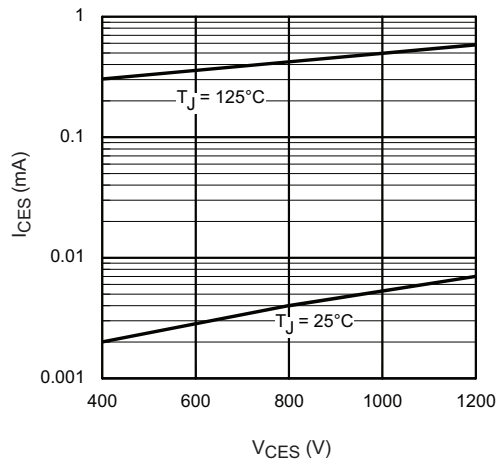


Fig. 11 - Typical Zero Gate Voltage Collector Current

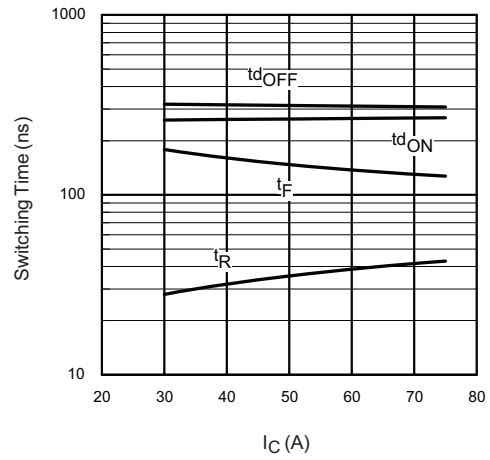
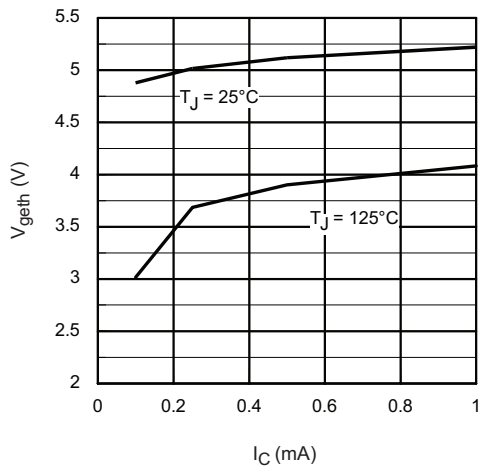
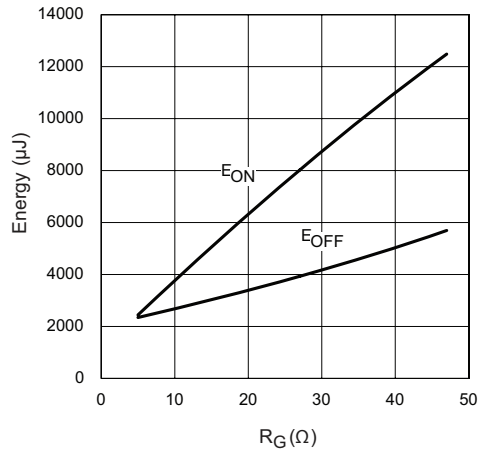
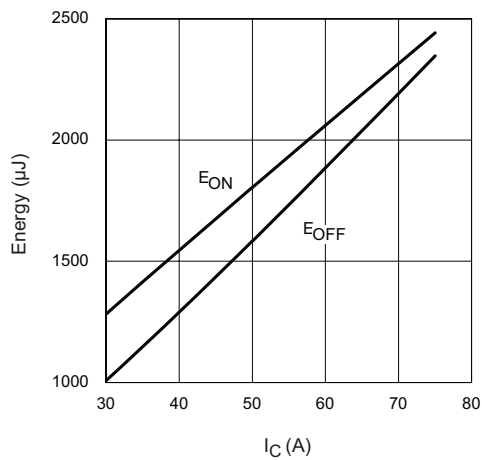
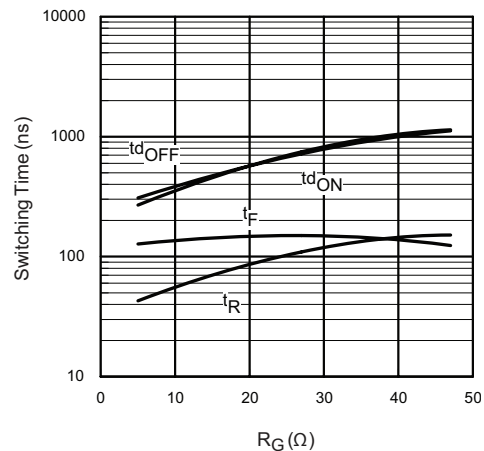

 Fig. 14 - Typical Switching Time vs. I_C
 $T_J = 125^\circ\text{C}$; $L = 500\ \mu\text{H}$; $V_{CC} = 600\ \text{V}$, $R_g = 5\ \Omega$; $V_{GE} = 15\ \text{V}$


Fig. 12 - Typical Threshold Voltage


 Fig. 15 - Typical Energy Loss vs. R_g
 $T_J = 125^\circ\text{C}$; $L = 500\ \mu\text{H}$; $V_{CC} = 600\ \text{V}$, $I_C = 75\ \text{A}$; $V_{GE} = 15\ \text{V}$

 Fig. 13 - Typical Energy Loss vs. I_C
 $T_J = 125^\circ\text{C}$; $L = 500\ \mu\text{H}$; $V_{CC} = 600\ \text{V}$, $R_g = 5\ \Omega$; $V_{GE} = 15\ \text{V}$

 Fig. 16 - Typical Switching Time vs. R_g
 $T_J = 125^\circ\text{C}$; $L = 500\ \mu\text{H}$; $V_{CC} = 600\ \text{V}$, $I_C = 75\ \text{A}$; $V_{GE} = 15\ \text{V}$

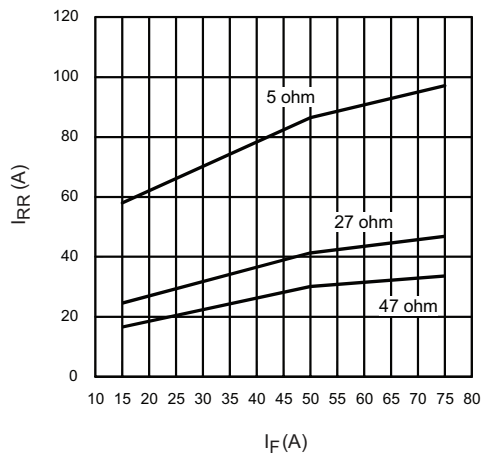


Fig. 17 - Typical Diode I_{RR} vs. I_F
 $T_J = 125^\circ\text{C}$

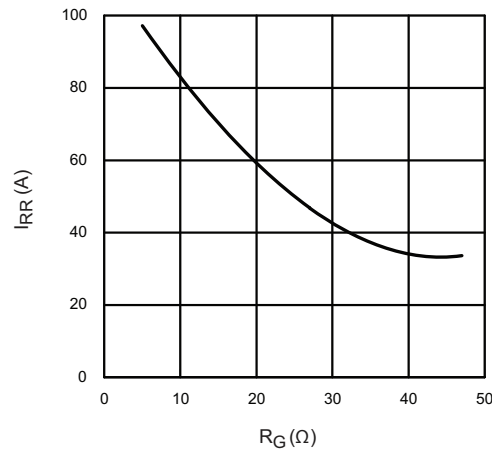


Fig. 19 - Typical Diode I_{RR} vs. R_G
 $T_J = 125^\circ\text{C}; I_F = 75\text{ A}$

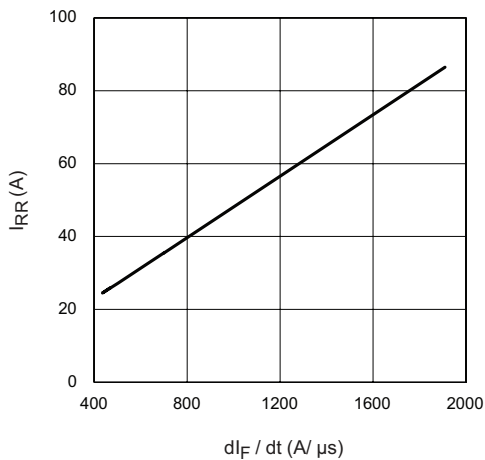


Fig. 18 - Typical Diode I_{RR} vs. dI_F/dt
 $V_{CC} = 600\text{ V}; I_F = 75\text{ A}$

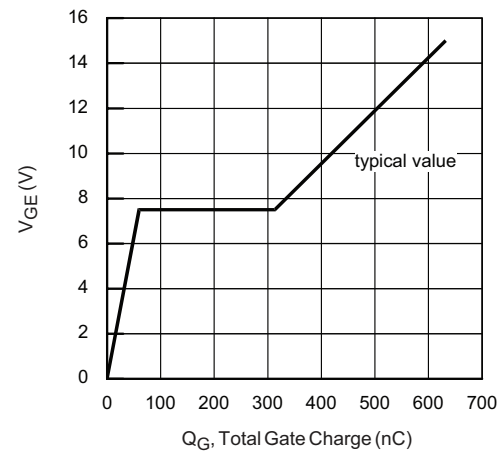


Fig. 20 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 5.0\text{ A}; L = 600\ \mu\text{H}$

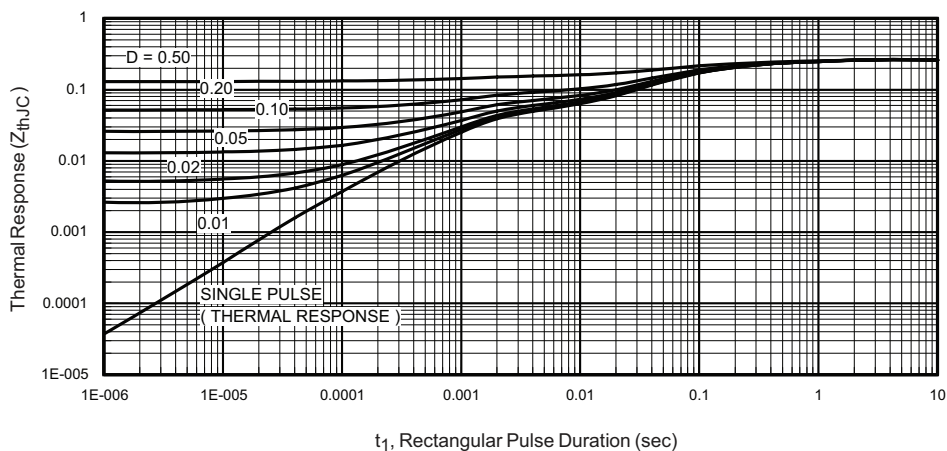


Fig. 21 - Maximum Transient Thermal Impedance, Junction to Case (IGBT)

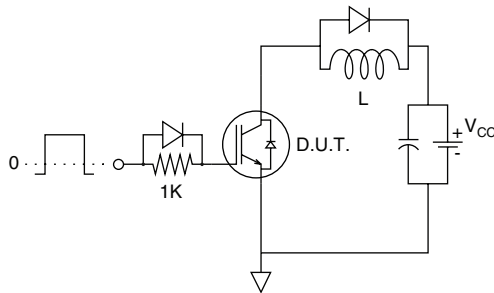


Fig. C.T.1 - Gate Charge Circuit (Turn-Off)

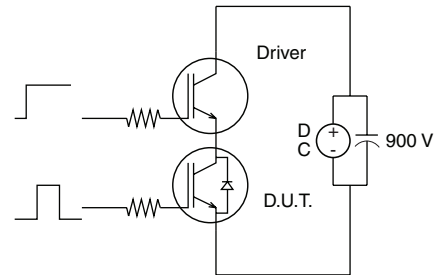


Fig. C.T.3 - S.C. SOA Circuit

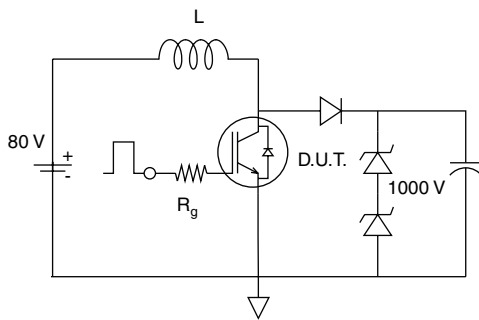


Fig. C.T.2 - RBSOA Circuit

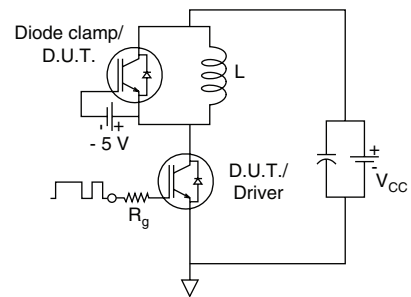


Fig. C.T.4 - Switching Loss Circuit

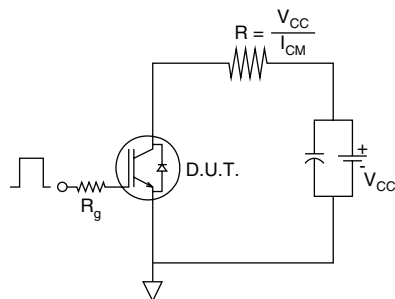


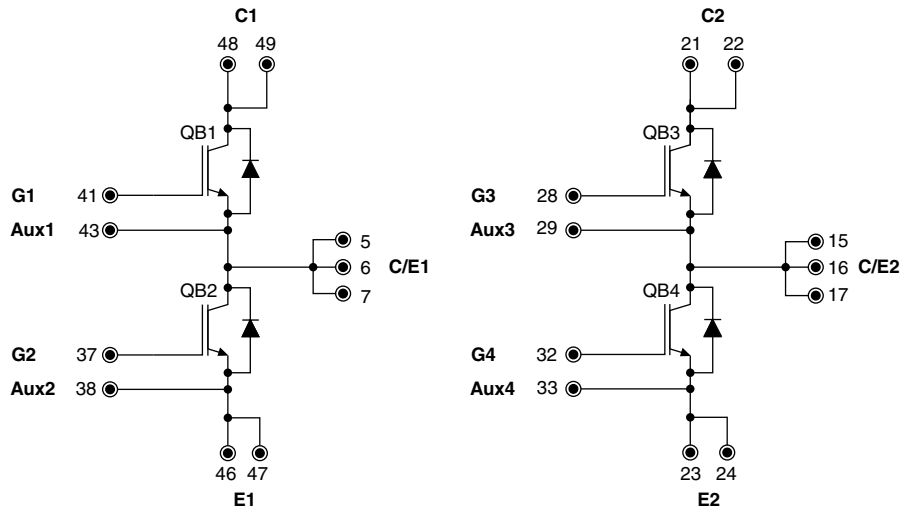
Fig. C.T.5 - Resistive Load Circuit

ORDERING INFORMATION TABLE

Device code	G	B	75	Y	F	120	U
	①	②	③	④	⑤	⑥	⑦

- 1** - Insulated gate bipolar transistor (IGBT)
- 2** - B = IGBT Generation 5
- 3** - Current rating (75 = 75 A)
- 4** - Circuit configuration (Y = Fourpack)
- 5** - Package indicator (F = ECONO2)
- 6** - Voltage rating (120 = 1200 V)
- 7** - Speed/type (U = Ultrafast IGBT)

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS

Dimensions

www.vishay.com/doc?95252



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